NSN 5961-00-835-7919

Unitized Semiconductor Devices - Page 1 of 1

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Inclosure Material:

Metal

Overall Length:

0.260 inches

Terminal Length:

0.500 inches

Overall Diameter:

0.335 inches

Component Name And Quantity:

2 transistor

Mounting Method:

Terminal

Terminal Circle Diameter:

0.200 inches

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

75.0 breakdown voltage, collector-to-base, emitter open all transistor and 40.0 breakdown voltage, collector-to-emitter, base open all transistor and 5.0 breakdown voltage, emitter-to-base, collector open all transistor

Current Rating Per Characteristic:

500.00 milliamperes source cutoff current all transistor

Power Rating Per Characteristic:

300.0 milliwatts small-signal input power, common-collector preset all transistor

Transfer Ratio:

30.0 static forward current transfer ratio, common-emitter all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

All transistor junction pattern arrangement: npn

Terminal Type And Quantity:

6 uninsulated wire lead

Specification Data:

80131-release3892 professional/industrial association specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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